

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"5247190".pn. "5399502".pn.	US-PGPUB; USPAT	OR	OFF	2007/02/12 11:11
L2	2	jp-10092576-\$.did. wo-9013148-\$.did.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/02/12 11:13
L3	1	1990-348684.NRAN.	DERWENT	OR	OFF	2007/02/12 11:17
L5	325	438/476.ccls.	US-PGPUB; USPAT	OR	OFF	2007/02/12 11:27
L6	172	(getter\$6 with (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride)) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2007/02/12 11:37
L7	32	L6 same (tft gate source drain)	US-PGPUB; USPAT	OR	ON	2007/02/12 11:37
L8	2411	438/151.ccls. 438/476.ccls. 438/791.ccls.	US-PGPUB; USPAT	OR	OFF	2007/02/12 11:42
L9	78	L8 and (getter\$6 same (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride))	US-PGPUB; USPAT	OR	ON	2007/02/12 11:42
L10	136	getter\$6 and (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/12 11:49
L11	27	L10 and (tft gate source drain)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/12 11:49
L12	8	getter\$6 same ((stress\$4 strain\$4 tensi\$6 compress\$6) with (dyne newton pascal pa mpa)) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2007/02/12 12:02
L13	40	getter\$6 same (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) same (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2007/02/12 12:07

## EAST Search History

L14	108	getter\$6 and (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/12 12:19
L15	23	getter\$6 same ((stress\$4 strain\$4 tensi\$6 compress\$6) with (dyne newton pascal pa mpa))	US-PGPUB; USPAT	OR	ON	2007/02/12 12:25
L16	32	(getter\$6 and (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))). clm.	US-PGPUB	OR	ON	2007/02/12 12:29